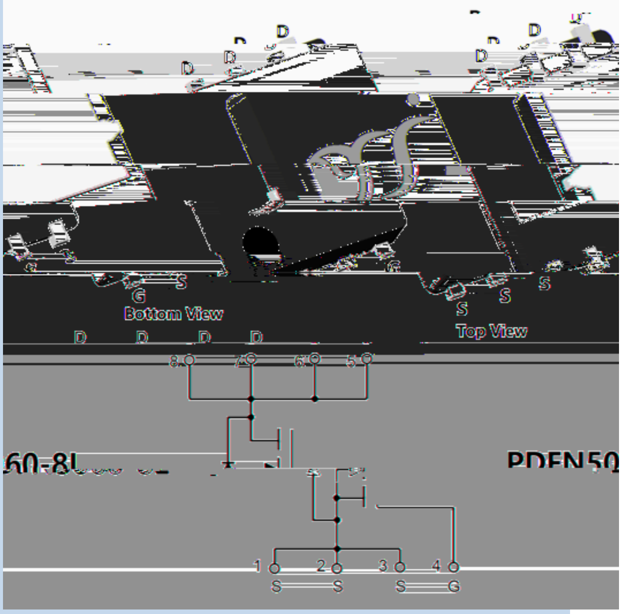
RoHS
COMPLIANT

# G300G04HRQ

## nent Mode Field Effect Transistor



## Product Summary

| | |
|---|---|
| ● $V_{DS}$ | 40V |
| ● $I_D$ | 300A |
| ● $R_{DS(ON)}$( at $V_{GS}$=10V) | 0.85mΩ |

- 100% EAS Tested
- 100% $V_{DS}$ Tested

## General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low RDS(OO ls ■ Absolute Maximum Ratings (TA=25 N unl

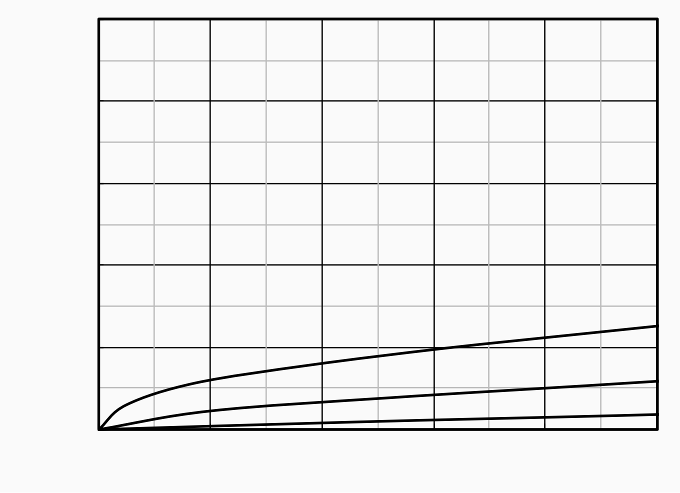
| Symbol | Limit | Unit |
|---|---|---|
| $V_{DS}$ | 40 | V |
| $V_{GS}$ | ±20 | V |
| $I_D$ | 43 | A |
| | 30 | |
| | 300 | |
| | 212 | |
| I | | |
| EAS | 1458 | mJ |
| $P_D$ | 3 | W |
| | 1.5 | |
| | 136 | |
| | 68 | |
| $T_J$ ,$T_{STG}$ | -55 +175 | |

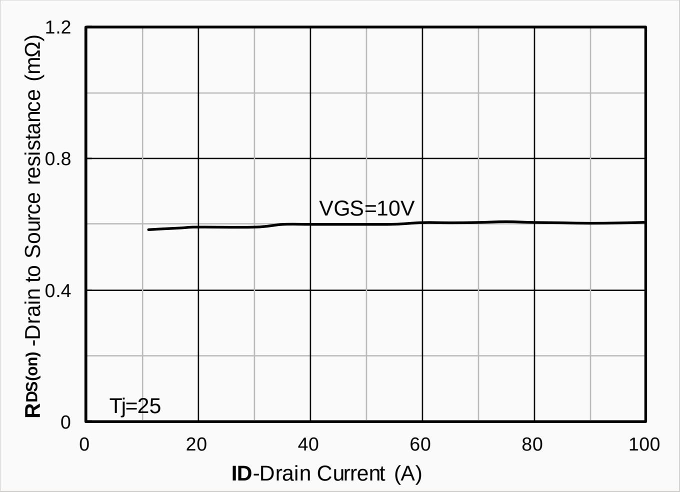
| PREFERED P/N | PACKING CODE | Marking | MINIMUM PACKAGE(pcs) | INNER BOX QUANTITY(pcs) | OUTER CARTON QUANTITY(pcs) | DELIVERY MODE |
|---|---|---|---|---|---|---|
| YJG300G04HRQ | F1 | G300G04HR | 5000 | 10000 | 100000 | 13“ reel |

## ■ Electrical Characteristics ($T_J$=25 unless otherwise noted)

| Parameter | Symbol | Conditions | Min | |
|---|---|---|---|---|

## ➢Typical Electrical and Thermal Characteristics Diagrams





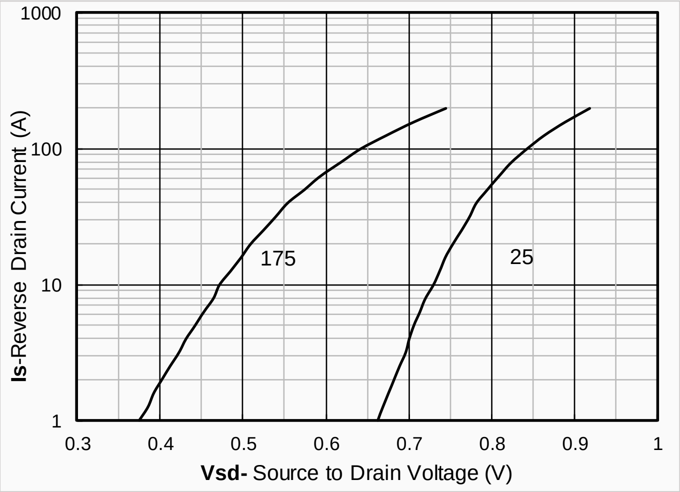
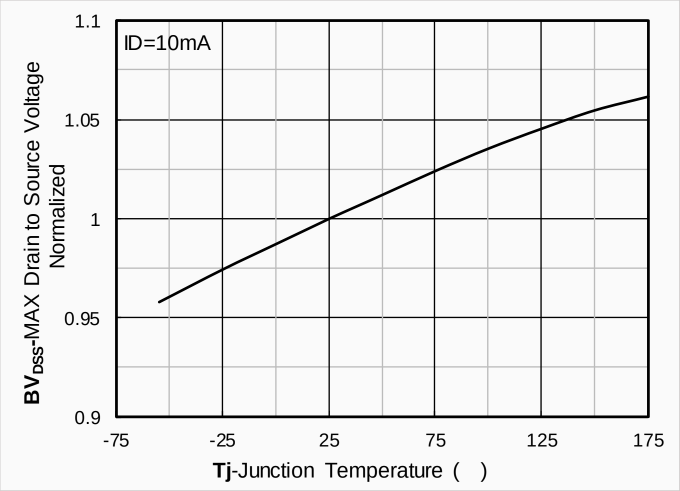


Figure 7. RDS(on) VS Drain Current

Figure 8. Forward characteristics of reverse diode



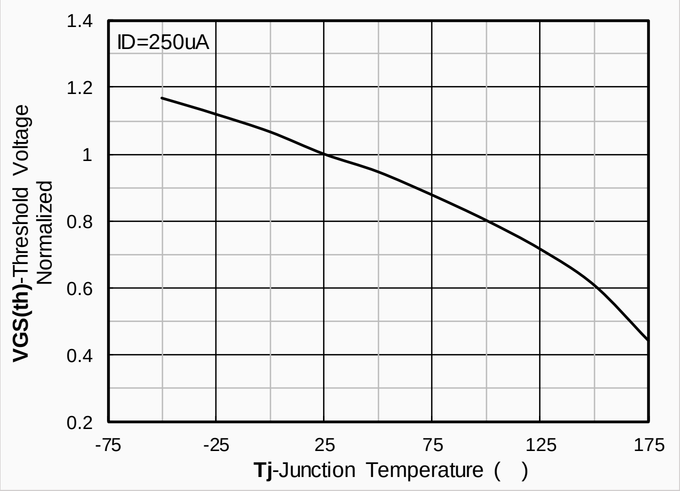
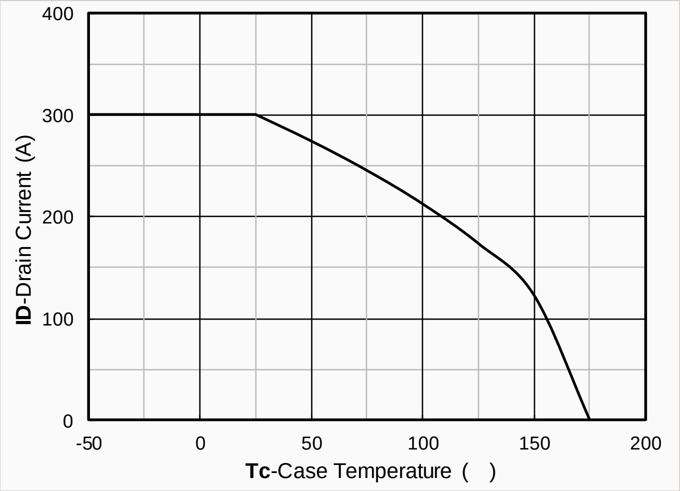
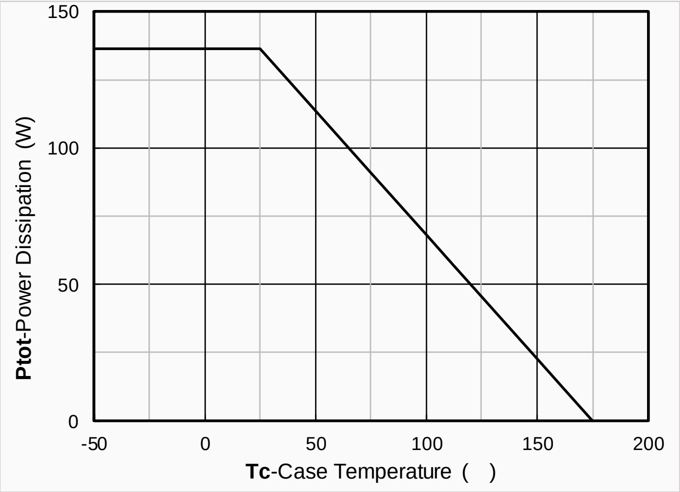
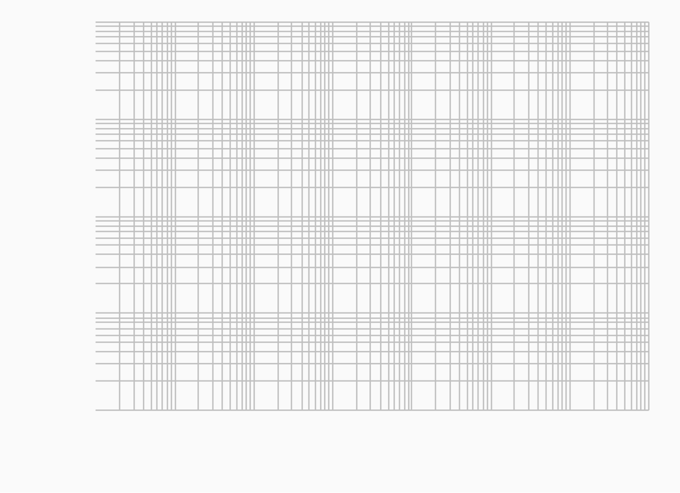


Figure 9. Normalized breakdown voltage

Figure 10. Normalized Threshold voltage







■

## 'LVFODLPHU

7KH LQIRUPDWLRQ SUHVHQWHG LQ WK\LV <DQJ]KRX <DQJMLH (OHFWURQLF 7HFKQRORJ\ [illegible]
ULJKW WR PDNH FKDQJHV [illegible] VSOD\HG KHUHLQ WR [illegible]
RWKHUZLVH

7KH SURGXFW OLVW [illegible] LFDO OLIH
VDYLQJ OLIHVXVWDLQLQJ [illegible]
VXFK LPSURSHU XVH RI VDOH

7KLV SXEOLFDWLRQ [illegible]
ZZZ \DQJMLH FRP [illegible] \RXU [illegible]